

4V Drive Pch + Pch MOSFET

QS8J4

Structure

Silicon P-channel MOSFET

Features

- 1) Low on-resistance.
- 2) High power package(TSMT8).
- 3) Low voltage drive(4V drive).

Application

Switching

Packaging specifications

	Package	Taping
Type	Code	TR
	Basic ordering unit (pieces)	3000
QS8J4		0

● Absolute maximum ratings (Ta = 25°C)

Parameter		Symbol	Limits	Unit	
Drain-source voltage		V_{DSS}	-30	V	
Gate-source voltage		V_{GSS}	±20	V	
Drain current	Continuous	I_{D}	±4	Α	
	Pulsed	I _{DP} *1	±16	А	
Source current (Body Diode)	Continuous	l _s	-1	А	
	Pulsed	I _{sp} *1	-16	А	
Power dissipation		P _D *2	1.5	W / TOTAL	
		' Б -	1.25	W / ELEMENT	
Channel temperature		Tch	150	°C	
Range of storage temperature		Tstg	-55 to +150	°C	

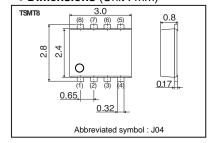
^{*1} Pw≤10µs, Duty cycle≤1%

Thermal resistance

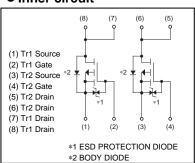
Parameter	Symbol	Limits	Unit
Channel to Ambient	Rth (ch-a)*	83.3	°C/W/TOTAL
Charlie to Ambient	Kill (Gli-a)	100	°C / W /ELEMENT

^{*} Each terminal mounted on a ceramic board.

Dimensions (Unit : mm)



• Inner circuit



^{*2} Each terminal mounted on a ceramic board.

● Electrical characteristics (Ta = 25°C)

<It is the same ratings for Tr1 and Tr2.>

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	I_{GSS}	-	-	±10	μA	$V_{GS}=\pm20V, V_{DS}=0V$
Drain-source breakdown voltage	V _{(BR)DSS}	-30	-	-	V	$I_D=-1$ mA, $V_{GS}=0$ V
Zero gate voltage drain current	I _{DSS}	1	-	-1	μA	V_{DS} =-30V, V_{GS} =0V
Gate threshold voltage	V _{GS (th)}	-1.0	-	-2.5	V	V_{DS} =-10V, I_{D} =-1mA
2	*		40	56		I _D =-4A, V _{GS} =-10V
Static drain-source on-state resistance	R _{DS (on)}	-	55	77	mΩ	I _D =-2A, V _{GS} =-4.5V
recicianos		-	60	84		$I_D=-2A$, $V_{GS}=-4V$
Forward transfer admittance	I Y _{fs} f*	3	-	-	S	I _D =-4A, V _{DS} =-10V
Input capacitance	C _{iss}	-	800	-	pF	V _{DS} =-10V
Output capacitance	C _{oss}	-	120	-	pF	V _{GS} =0V
Reverse transfer capacitance	C _{rss}	-	110	-	pF	f=1MHz
Turn-on delay time	t _{d(on)} *		8	-	ns	I _D =-2A, V _D ; -15V
Rise time	t _r *	1	20	-	ns	V _{GS} =-10V
Turn-off delay time	t _{d(off)} *	-	80	-	ns	$R_L=7.5\Omega$
Fall time	t _f *	ı	50	-	ns	$R_G=10\Omega$
Total gate charge	Q _g *	1	8.4	-	nC	I _D =−4A, V _D ; −15V
Gate-source charge	Q _{gs} *	-	3.0	-	nC	V _{GS} =-5V
Gate-drain charge	Q _{gd} *	-	3.5	-	nC	$R_L=3.8\Omega$, $R_G=10\Omega$

^{*}Pulsed

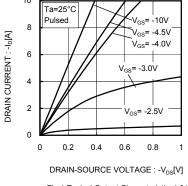
●Body diode characteristics (Source-Drain) (Ta = 25°C)

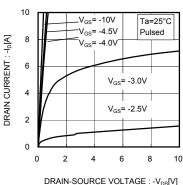
<It is the same ratings for Tr1 and Tr2.>

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward Voltage	V _{SD} *	-	-	-1.2	V	$I_s=-4A$, $V_{GS}=0V$

^{*}Pulsed

Electrical characteristic curves





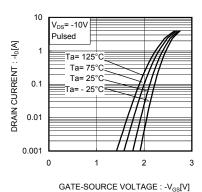
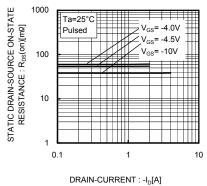


Fig.1 Typical Output Characteristics(I)

Fig.2 Typical Output Characteristics(II)

Fig.3 Typical Transfer Characteristics



1000 STATIC DRAIN-SOURCE ON-STATE V_{GS}= -10V a=125°0 R_{DS}(on)[mΩ] Ta=75°C Ta=25°C 100 Ta= -25°C RESISTANCE 10 0.1 DRAIN-CURRENT : -ID[A]

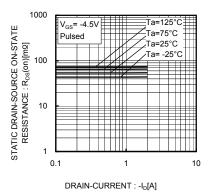


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current(I)

Fig.5 Static Drain-Source On-State Resistance vs. Drain Current(II)

Fig.6 Static Drain-Source On-State Resistance vs. Drain Current(III)

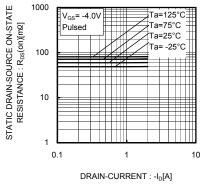


Fig.7 Static Drain-Source On-State Resistance vs. Drain Current(IV)

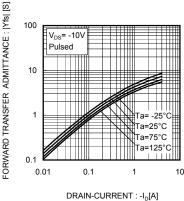


Fig.8 Forward Transfer Admittance vs. Drain Current

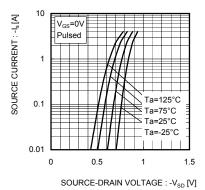
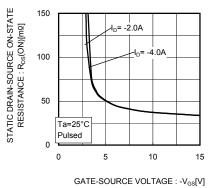
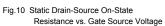


Fig.9 Reverse Drain Current vs. Sourse-Drain Voltage





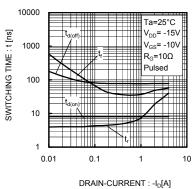
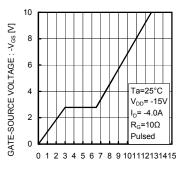
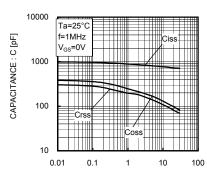


Fig.11 Switching Characteristics



TOTAL GATE CHARGE : Qg [nC] Fig.12 Dynamic Input Characteristics



DRAIN-SOURCE VOLTAGE : -V_{DS}[V]
Fig.13 Typical Capacitance
vs. Drain-Source Voltage

Data Sheet

Measurement circuits

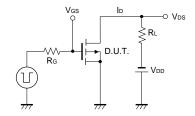


Fig.1-1 Switching Time Measurement Circuit

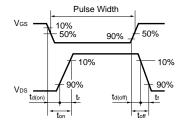


Fig.1-2 Switching Waveforms

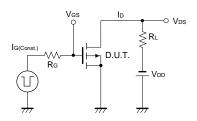


Fig.2-1 Gate Charge Measurement Circuit

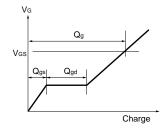


Fig.2-2 Gate Charge Waveform

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